HGTP12N60C3, HGT1S12N60C3, HGT1S12N60C3S

January 1997

24A, 600V, UFS Series N-Channel IGBTs

Features

- 24A, 600V at $T_C = 25^oC$
- 600V Switching SOA Capability
- Typical Fall Time . . . . . 230ns at $T_J = 150^oC$
- Short Circuit Rating
- Low Conduction Loss

Ordering Information

PART NUMBER	PACKAGE	BRAND
HGTP12N60C3	TO-220AB	P12N60C3
HGT1S12N60C3	TO-262AA	S12N60C3
HGT1S12N60C3S	TO-263AB	S12N60C3

NOTE: When ordering, use the entire part number. Add the suffix 9A to obtain the TO-263AB variant in Tape and Reel, i.e., HGT1S12N60C3S9A.

Formerly Developmental Type TA49123.

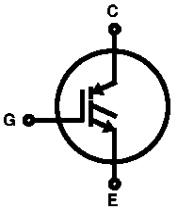
Description

The HGTP12N60C3, HGT1S12N60C3 and HGT1S12N60C3S are MOS gated high voltage switching devices combining the best features of MOSFETs and bipolar transistors. These devices have the high input impedance of a MOSFET and the low on-state conduction loss of a bipolar transistor. The much lower on-state voltage drop varies only moderately between 25^oC and 150^oC.

The IGBT is ideal for many high voltage switching applications operating at moderate frequencies where low conduction losses are essential, such as: AC and DC motor controls, power supplies and drivers for solenoids, relays and contactors.

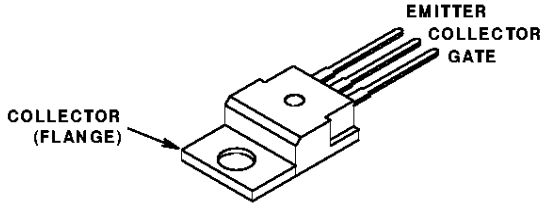
Terminal Diagram

N-CHANNEL ENHANCEMENT MODE

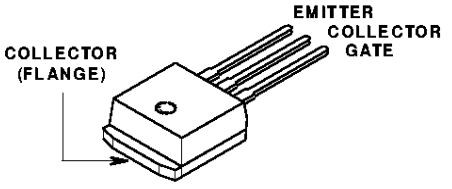


Packaging

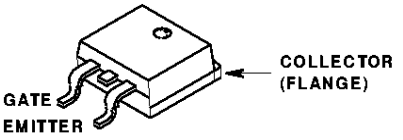
JEDEC TO-220AB



JEDEC TO-262AA



JEDEC TO-263AB



HARRIS SEMICONDUCTOR IGBT PRODUCT IS COVERED BY ONE OR MORE OF THE FOLLOWING U.S. PATENTS:

4,364,073	4,417,385	4,430,792	4,443,931	4,466,176	4,516,143	4,532,534	4,567,641
4,587,713	4,598,461	4,605,948	4,618,872	4,620,211	4,631,564	4,639,754	4,639,762
4,641,162	4,644,637	4,682,195	4,684,413	4,694,313	4,717,679	4,743,952	4,783,690
4,794,432	4,801,986	4,803,533	4,809,045	4,809,047	4,810,665	4,823,176	4,837,606
4,860,080	4,883,767	4,888,627	4,890,143	4,901,127	4,904,609	4,933,740	4,963,951
4,969,027							

CAUTION: These devices are sensitive to electrostatic discharge. Users should follow proper ESD Handling Procedures.

File Number **4040.3**

Absolute Maximum Ratings $T_C = 25^oC$, Unless Otherwise Specified

	HGTP12N60C3, HGT1S12N60C3, HGT1S12N60C3S	UNITS
Collector-Emitter Voltage . . . . . BV_{CES}	600	V
Collector Current Continuous		
At $T_C = 25^oC$ . . . . . I_{C25}	24	A
At $T_C = 110^oC$ . . . . . I_{C110}	12	A
Collector Current Pulsed (Note 1) . . . . . I_{CM}	96	A
Gate-Emitter Voltage Continuous. . . . . V_{GES}	±20	V
Gate-Emitter Voltage Pulsed . . . . . V_{GEM}	±30	V
Switching Safe Operating Area at $T_J = 150^oC$, Figure 14 . . . . . SSOA	24A at 600V	
Power Dissipation Total at $T_C = 25^oC$ . . . . . P_D	104	W
Power Dissipation Derating $T_C > 25^oC$	0.83	$W/^oC$
Reverse Voltage Avalanche Energy. . . . . E_{ARV}	100	mJ
Operating and Storage Junction Temperature Range . . . . . T_J, T_{STG}	-40 to 150	^oC
Maximum Lead Temperature for Soldering . . . . . T_L	260	^oC
Short Circuit Withstand Time (Note 2) at $V_{GE} = 15V$ . . . . . t_{SC}	4	µs
Short Circuit Withstand Time (Note 2) at $V_{GE} = 10V$ . . . . . t_{SC}	13	µs

NOTES:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. $V_{CE(PK)} = 360V$, $T_J = 125^oC$, $R_{GE} = 25\Omega$.

Electrical Specifications $T_C = 25^oC$, Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CONDITIONS		MIN	TYP	MAX	UNITS
Collector-Emitter Breakdown Voltage	BV_{CES}	$I_C = 250\mu A$, $V_{GE} = 0V$		600	-	-	V
Emitter-Collector Breakdown Voltage	BV_{ECS}	$I_C = 10mA$, $V_{GE} = 0V$		24	30	-	V
Collector-Emitter Leakage Current	I_{CES}	$V_{CE} = BV_{CES}$	$T_C = 25^oC$	-	-	250	µA
		$V_{CE} = BV_{CES}$	$T_C = 150^oC$	-	-	1.0	mA
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	$I_C = I_{C110}$, $V_{GE} = 15V$	$T_C = 25^oC$	-	1.65	2.0	V
			$T_C = 150^oC$	-	1.85	2.2	V
Gate-Emitter Threshold Voltage	$V_{GE(TH)}$	$I_C = 250\mu A$, $V_{CE} = V_{GE}$	$T_C = 25^oC$	3.0	5.0	6.0	V
Gate-Emitter Leakage Current	I_{GES}	$V_{GE} = \pm 20V$		-	-	±100	nA
Switching SOA	SSOA	$T_J = 150^oC$, $R_G = 25\Omega$, $V_{GE} = 15V$, $L = 100\mu H$	$V_{CE(PK)} = 480V$	80	-	-	A
			$V_{CE(PK)} = 600V$	24	-	-	A
Gate-Emitter Plateau Voltage	V_{GEP}	$I_C = I_{C110}$, $V_{CE} = 0.5\ BV_{CES}$		-	7.6	-	V
On-State Gate Charge	$Q_{G(ON)}$	$I_C = I_{C110}$, $V_{CE} = 0.5\ BV_{CES}$	$V_{GE} = 15V$	-	48	55	nC
			$V_{GE} = 20V$	-	62	71	nC
Current Turn-On Delay Time	$t_{D(ON)I}$	$T_J = 150^oC$, $I_{CE} = I_{C110}$, $V_{CE(PK)} = 0.8\ BV_{CES}$, $V_{GE} = 15V$, $R_G = 25\Omega$, $L = 100\mu H$		-	14	-	ns
Current Rise Time	t_{RI}			-	16	-	ns
Current Turn-Off Delay Time	$t_{D(OFF)I}$			-	270	400	ns
Current Fall Time	t_{FI}			-	210	275	ns
Turn-On Energy	E_{ON}			-	380	-	µJ
Turn-Off Energy (Note 3)	E_{OFF}			-	900	-	µJ
Thermal Resistance	$R_{\theta JC}$			-	-	1.2	$^oC/W$

NOTE:

3. Turn-Off Energy Loss (E_{OFF}) is defined as the integral of the instantaneous power loss starting at the trailing edge of the input pulse and ending at the point where the collector current equals zero ($I_{CE} = 0A$). The HGTP12N60C3, HGT1S12N60C3 and HGT1S12N60C3S were tested per JEDEC standard No. 24-1 Method for Measurement of Power Device Turn-Off Switching Loss. This test method produces the true total Turn-Off Energy Loss. Turn-On losses include diode losses.

Typical Performance Curves

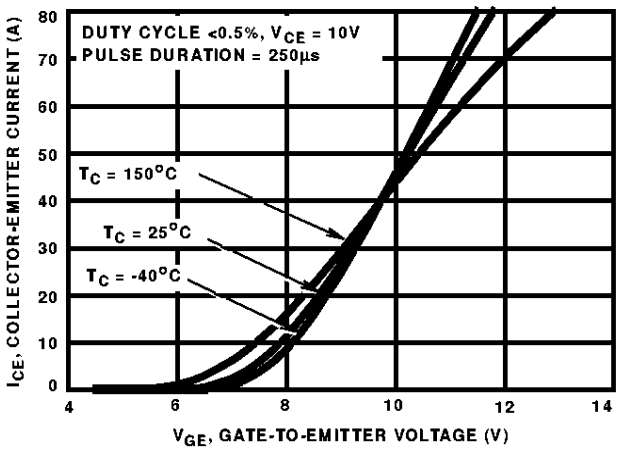


FIGURE 1. TRANSFER CHARACTERISTICS

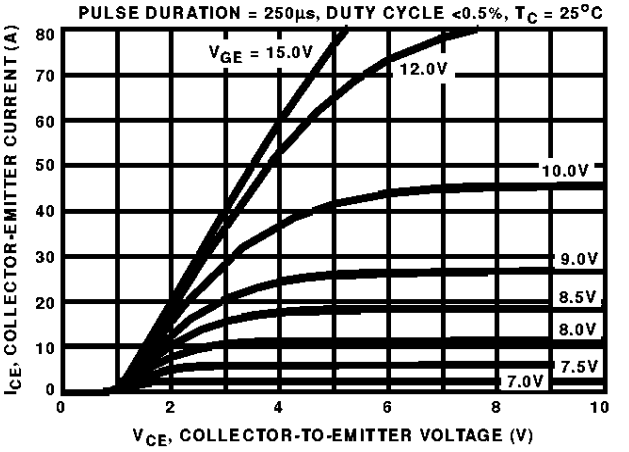


FIGURE 2. SATURATION CHARACTERISTICS

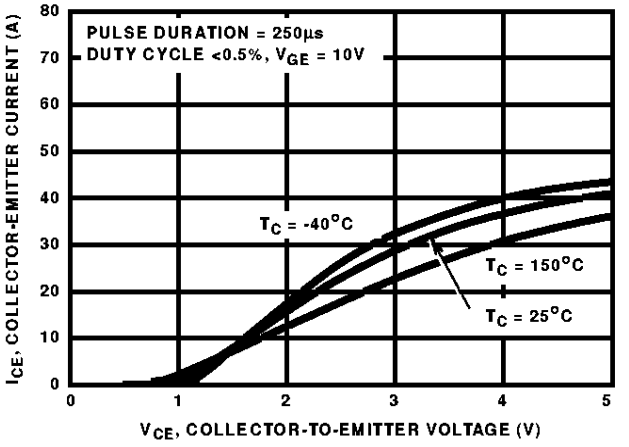


FIGURE 3. COLLECTOR-EMITTER ON-STATE VOLTAGE

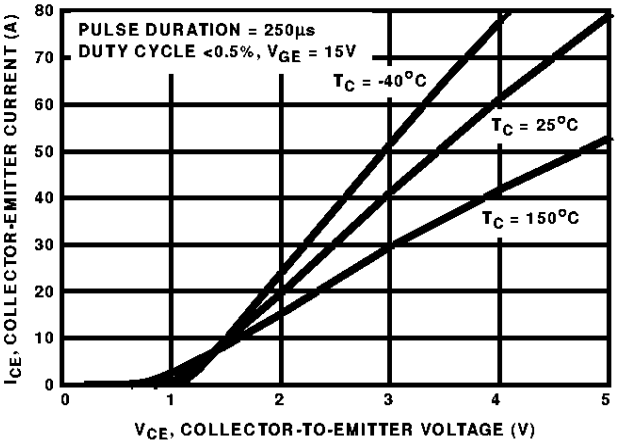


FIGURE 4. COLLECTOR-EMITTER ON-STATE VOLTAGE

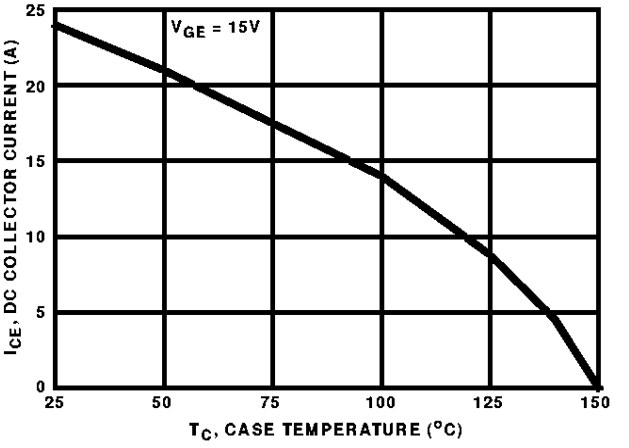


FIGURE 5. DC COLLECTOR CURRENT AS A FUNCTION OF CASE TEMPERATURE

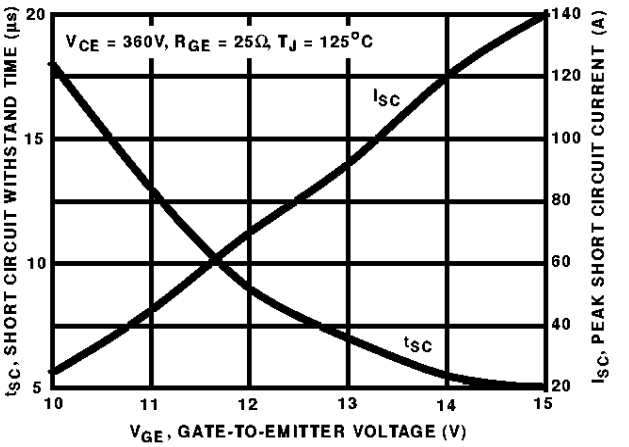


FIGURE 6. SHORT CIRCUIT WITHSTAND TIME

Typical Performance Curves (Continued)

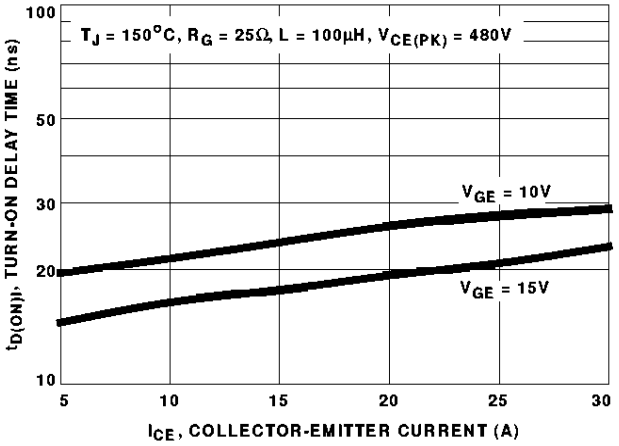


FIGURE 7. TURN-ON DELAY TIME AS A FUNCTION OF COLLECTOR-EMITTER CURRENT

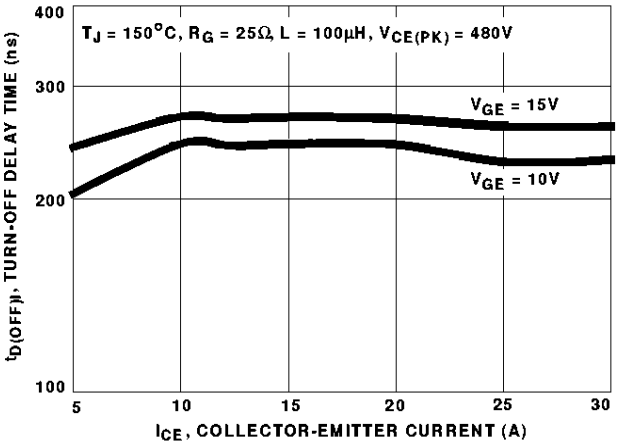


FIGURE 8. TURN-OFF DELAY TIME AS A FUNCTION OF COLLECTOR-EMITTER CURRENT

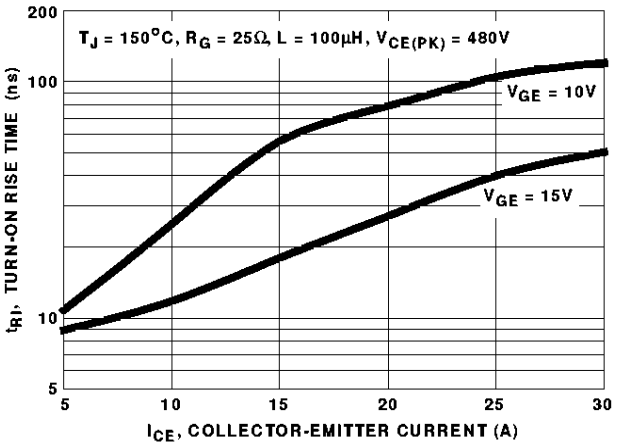


FIGURE 9. TURN-ON RISE TIME AS A FUNCTION OF COLLECTOR-EMITTER CURRENT

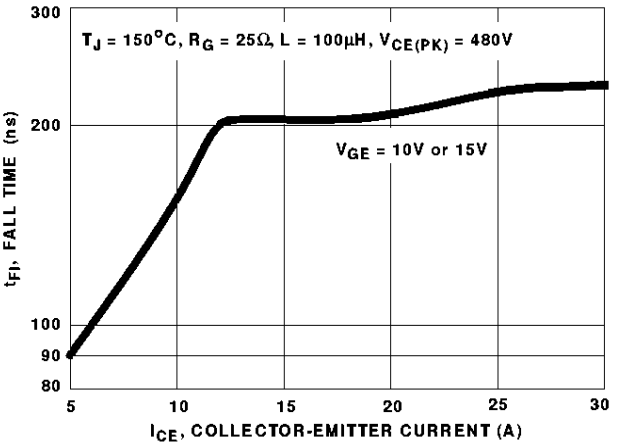


FIGURE 10. TURN-OFF FALL TIME AS A FUNCTION OF COLLECTOR-EMITTER CURRENT

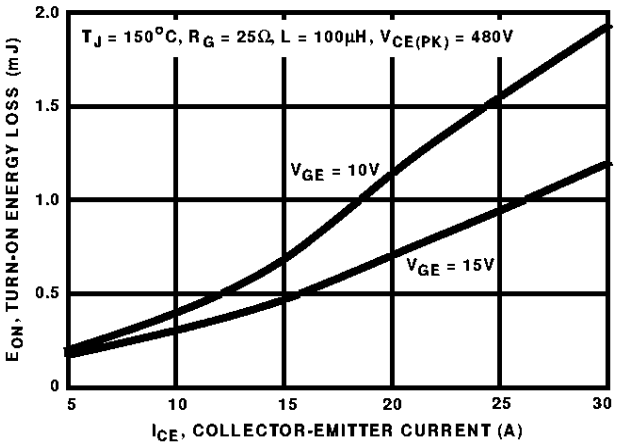


FIGURE 11. TURN-ON ENERGY LOSS AS A FUNCTION OF COLLECTOR-EMITTER CURRENT

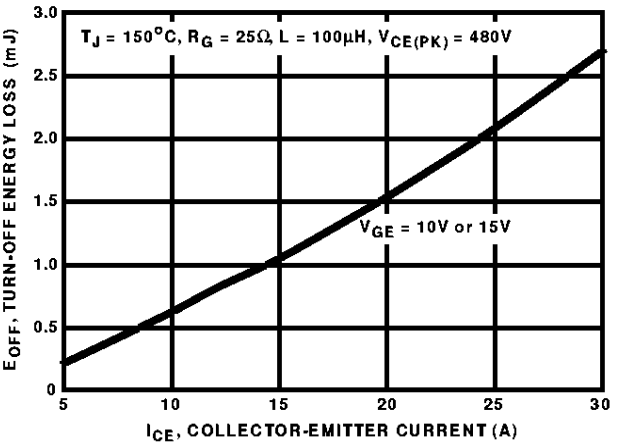


FIGURE 12. TURN-OFF ENERGY LOSS AS A FUNCTION OF COLLECTOR-EMITTER CURRENT

Typical Performance Curves (Continued)

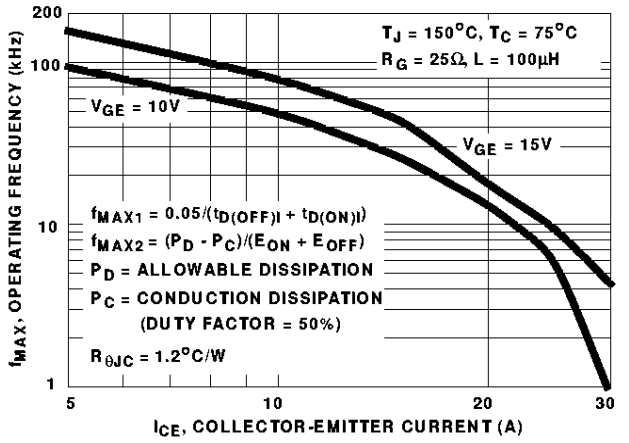


FIGURE 13. OPERATING FREQUENCY AS A FUNCTION OF COLLECTOR-EMITTER CURRENT

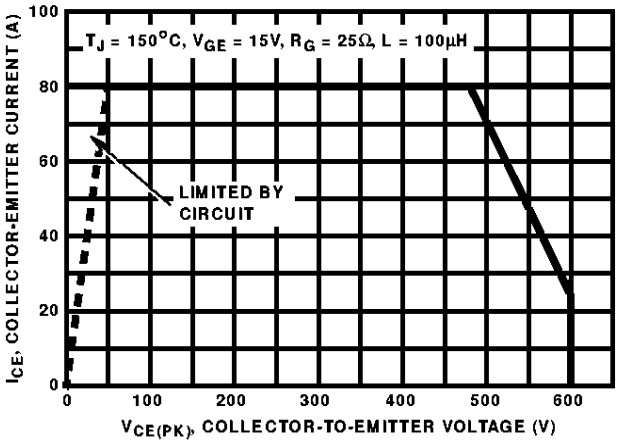


FIGURE 14. SWITCHING SAFE OPERATING AREA

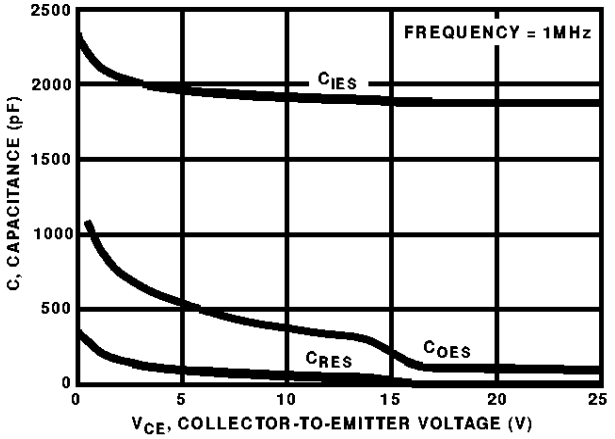


FIGURE 15. CAPACITANCE AS A FUNCTION OF COLLECTOR-EMITTER VOLTAGE

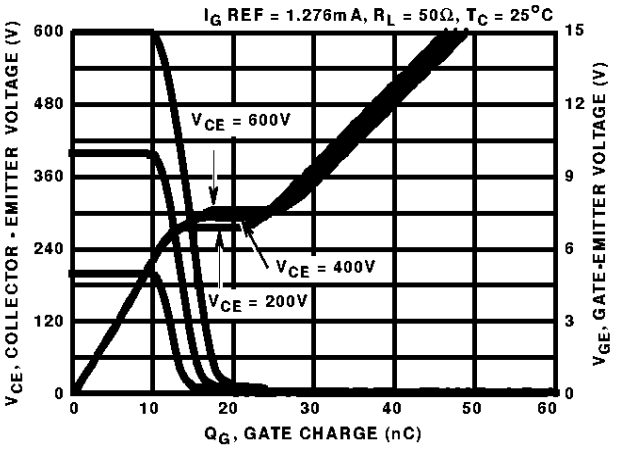


FIGURE 16. GATE CHARGE WAVEFORMS

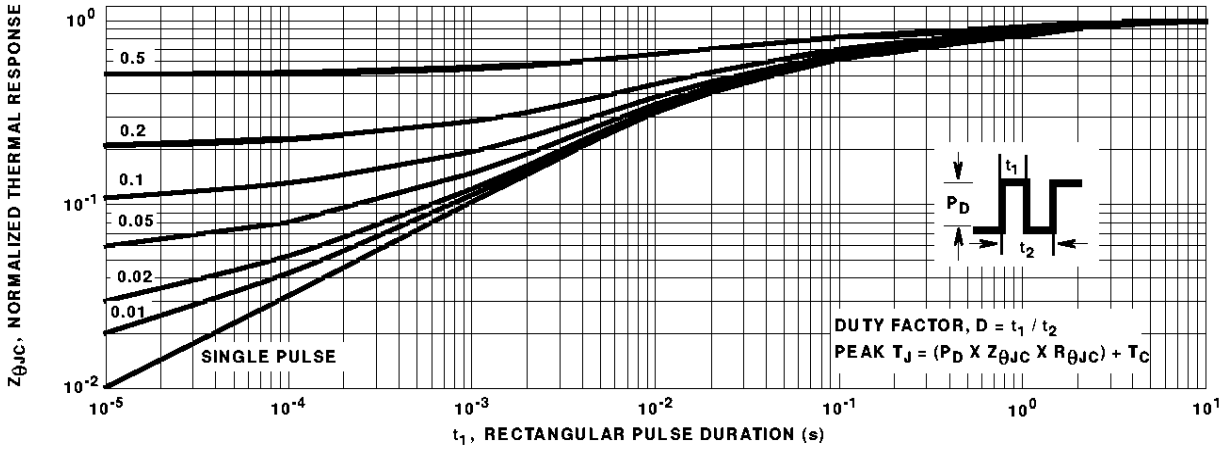


FIGURE 17. IGBT NORMALIZED TRANSIENT THERMAL IMPEDANCE, JUNCTION TO CASE

Test Circuit and Waveform

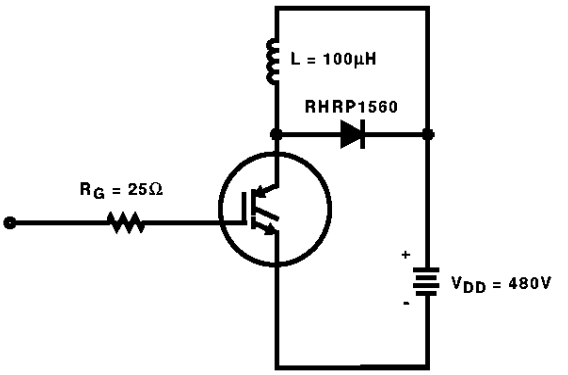


FIGURE 18. INDUCTIVE SWITCHING TEST CIRCUIT

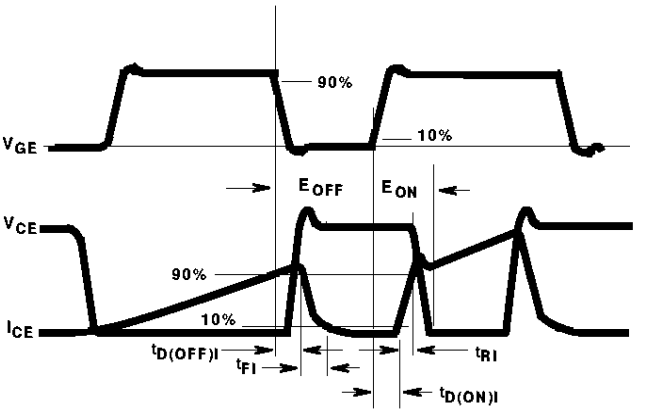


FIGURE 19. SWITCHING TEST WAVEFORMS

Handling Precautions for IGBTs

Insulated Gate Bipolar Transistors are susceptible to gate-insulation damage by the electrostatic discharge of energy through the devices. When handling these devices, care should be exercised to assure that the static charge built in the handler's body capacitance is not discharged through the device. With proper handling and application procedures, however, IGBTs are currently being extensively used in production by numerous equipment manufacturers in military, industrial and consumer applications, with virtually no damage problems due to electrostatic discharge. IGBTs can be handled safely if the following basic precautions are taken:

1. Prior to assembly into a circuit, all leads should be kept shorted together either by the use of metal shorting springs or by the insertion into conductive material such as "ECCOSORBD™ LD26" or equivalent.
2. When devices are removed by hand from their carriers, the hand being used should be grounded by any suitable means - for example, with a metallic wristband.
3. Tips of soldering irons should be grounded.
4. Devices should never be inserted into or removed from circuits with power on.
5. **Gate Voltage Rating** - Never exceed the gate-voltage rating of V_{GEM}. Exceeding the rated V_{GE} can result in permanent damage to the oxide layer in the gate region.
6. **Gate Termination** - The gates of these devices are essentially capacitors. Circuits that leave the gate open-circuited or floating should be avoided. These conditions can result in turn-on of the device due to voltage buildup on the input capacitor due to leakage currents or pickup.
7. **Gate Protection** - These devices do not have an internal monolithic zener diode from gate to emitter. If gate protection is required an external zener is recommended.

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Operating Frequency Information

Operating frequency information for a typical device Figure 13) is presented as a guide for estimating device performance for a specific application. Other typical frequency vs collector current (I_{CE}) plots are possible using the information shown for a typical unit in Figures 4, 7, 8, 11 and 12. The operating frequency plot (Figure 13) of a typical device shows f_{MAX1} or f_{MAX2} whichever is smaller at each point. The information is based on measurements of a typical device and is bounded by the maximum rated junction temperature.

f_{MAX1} is defined by $f_{MAX1} = 0.05/(t_{D(OFF)I} + t_{D(ON)I})$. Deadtime (the denominator) has been arbitrarily held to 10% of the on- state time for a 50% duty factor. Other definitions are possible. $t_{D(OFF)I}$ and $t_{D(ON)I}$ are defined in Figure 19. Device turn-off delay can establish an additional frequency limiting condition for an application other than T_{JMAX}. $t_{D(OFF)I}$ is important when controlling output ripple under a lightly loaded condition.

f_{MAX2} is defined by $f_{MAX2} = (P_D - P_C)/(E_{OFF} + E_{ON})$. The allowable dissipation (P_D) is defined by $P_D = (T_{JMAX} - T_C)/R_{\theta JC}$. The sum of device switching and conduction losses must not exceed P_D. A 50% duty factor was used (Figure 13) and the conduction losses (P_C) are approximated by $P_C = (V_{CE} \times I_{CE})/2$.

E_{ON} and E_{OFF} are defined in the switching waveforms shown in Figure 19. E_{ON} is the integral of the instantaneous power loss ($I_{CE} \times V_{CE}$) during turn-on and E_{OFF} is the integral of the instantaneous power loss ($I_{CE} \times V_{CE}$) during turn-off. All tail losses are included in the calculation for E_{OFF}; i.e. the collector current equals zero ($I_{CE} = 0$).